

描述 / Descriptions

N 沟道 TO-252 塑封封装场效应管。

N-Channel MOSFET in a TO-252 Plastic Package.

特征 / Features

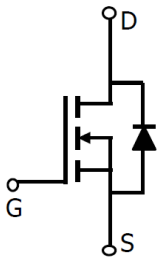
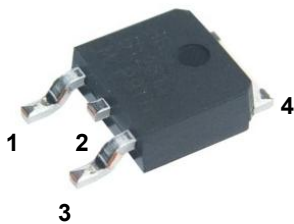
低栅电荷,导通电阻低,快速切换应用的优化。无卤产品。

Low gate charge, Low $R_{DS(on)}$, Optimized for fast-switching applications. Halogen-free Product.

用途 / Applications

用于低压电路如:汽车电路、DC/DC 转换、便携式产品的电源高效转换。

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1 : G

PIN 2、4 : D

PIN 3 : S

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	200	V
Drain Current ^G	$I_D(T_C=25^{\circ}C)$	18	A
	$I_D(T_C=100^{\circ}C)$	13	A
Drain Current - Pulsed ^C	I_{DM}	45	A
Gate-Source Voltage	V_{GSS}	±20	V
Single Pulsed Avalanche Energy(L=10mH)	E_{AS}	125	mJ
Avalanche Current ^C (L=10mH)	I_{AS}	9.5	A
Power Dissipation ^B	$P_D(T_C=25^{\circ}C)$	102	W
	$P_D(T_C=100^{\circ}C)$	51	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	°C/W
Maximum Junction-to-Ambient ^{AD}	Steady-State		
Maximum Junction-to-Case	Steady-State		
		$R_{\theta JC}$	0.82

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	200			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=200V$ $V_{GS}=0V$			1	μA
		$V_{DS}=200V$ $T_J=55^{\circ}C$			5	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0		3.0	V
Total gate charge	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=9A$		130	170	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=18A$			1.45	V

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		6.5		Ω
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		832		pF
Output Capacitance	C_{oss}			149		
Reverse Transfer Capacitance	C_{rss}			65		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=100V$ $I_D=18A$		27	40	nC
Total Gate Charge	$Q_{g(4.5V)}$			12	20	
Gate Source Charge	Q_{gs}			7		
Gate Drain Charge	Q_{gd}			3		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=100V$ $R_L=5.5\Omega$ $R_{GEN}=3\Omega$		8		ns
Turn-On Rise Time	t_r			10		ns
Turn-Off Delay Time	$t_{d(off)}$			30		ns
Turn-Off Fall Time	t_f			4		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F=18A$ $dI/dt=500A/\mu s$		60		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=18A$ $dI/dt=500A/\mu s$		800		nC

A: The value of $R_{\theta JA}$ is measured with the device in a still air environment with $T_A=25^\circ C$.

B. The power dissipation PD is based on $T_J(MAX)=150^\circ C$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_J(MAX)=150^\circ C$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300 \mu s$ pulses, duty cycle 0.5%max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_J(MAX)=150^\circ C$.

G. The maximum current rating is limited by bond-wires.

电参数曲线图 / Electrical Characteristic Curve

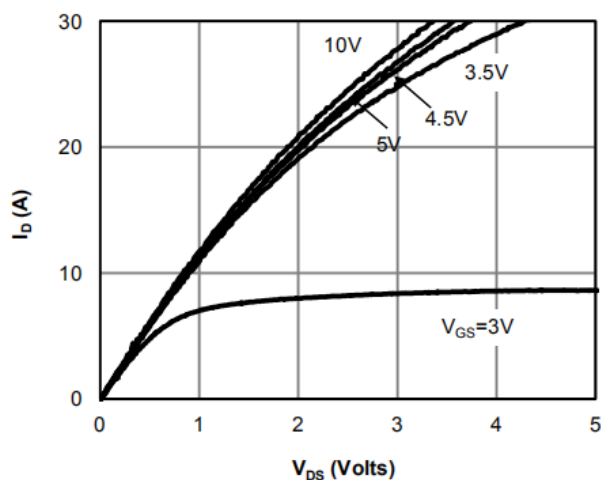


Figure 1: On-Region Characteristics

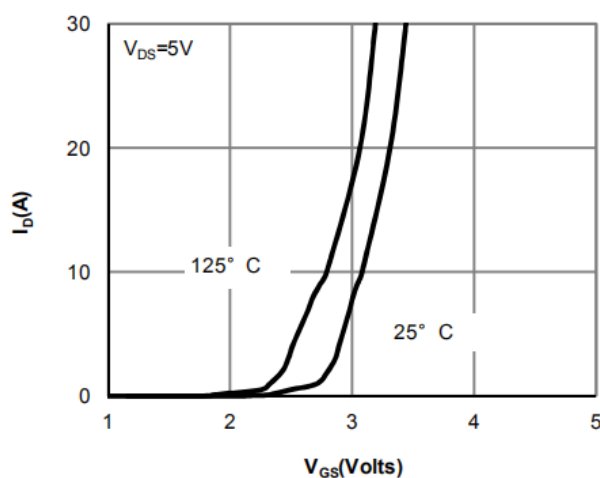


Figure 2: Transfer Characteristics

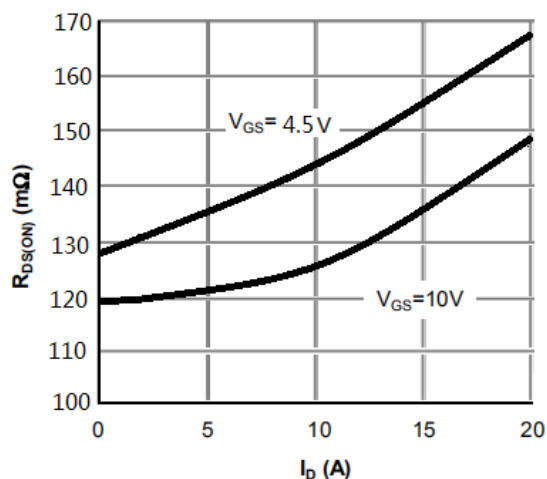


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

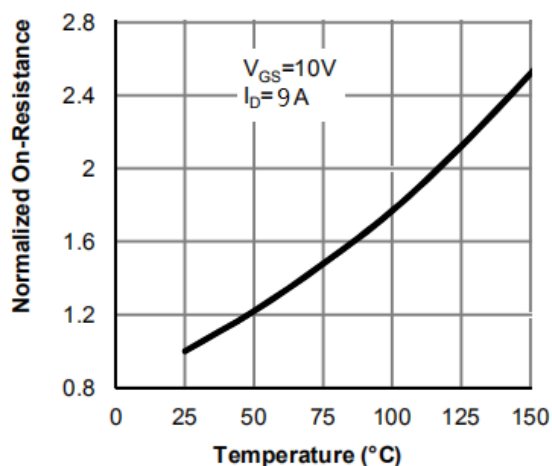


Figure 4: On-Resistance vs. Junction Temperature

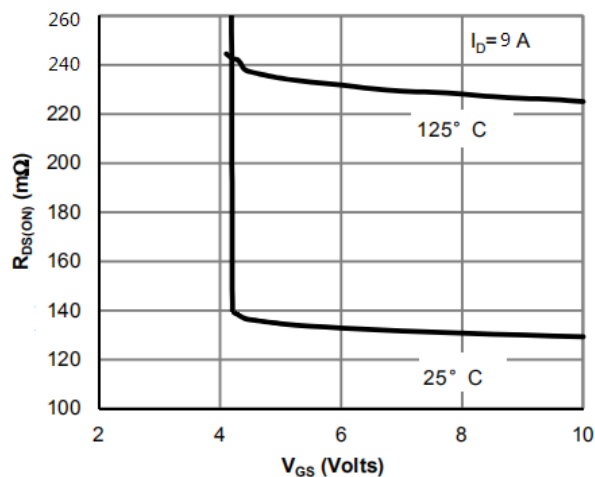


Figure 5: On-Resistance vs. Gate-Source Voltage

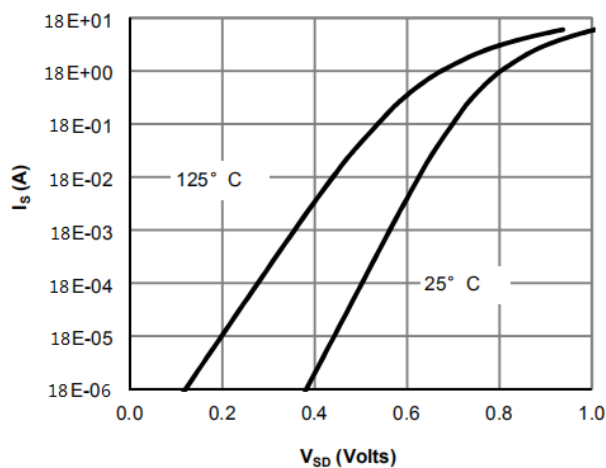
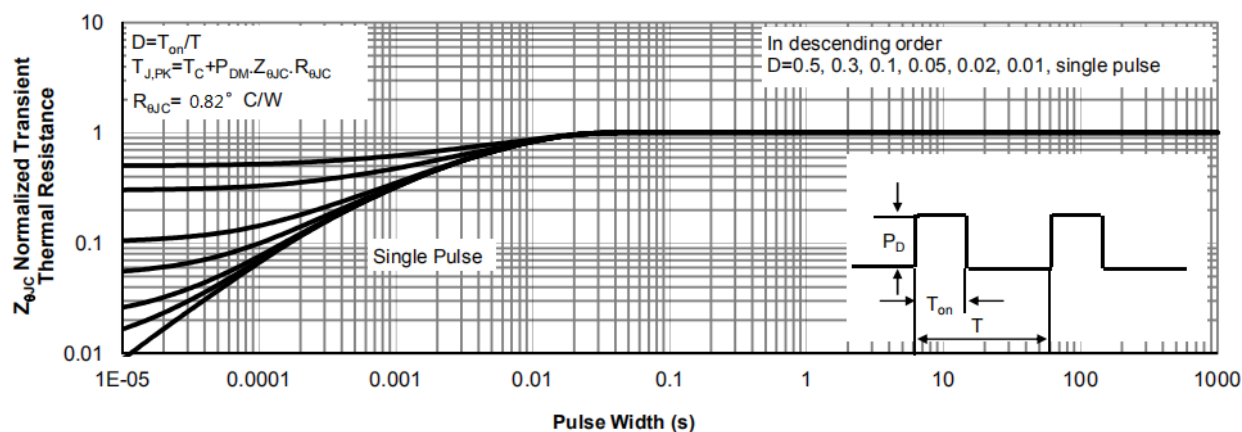
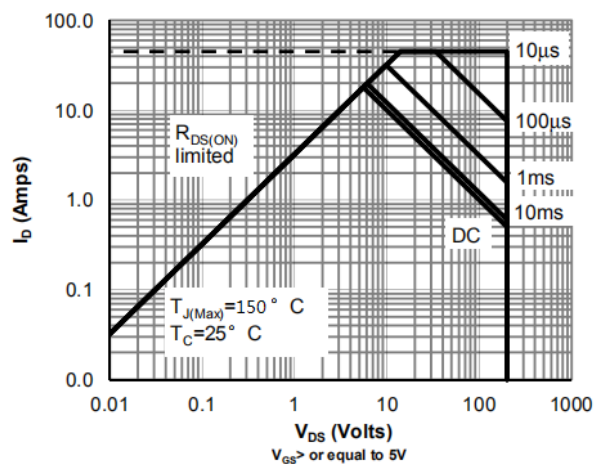
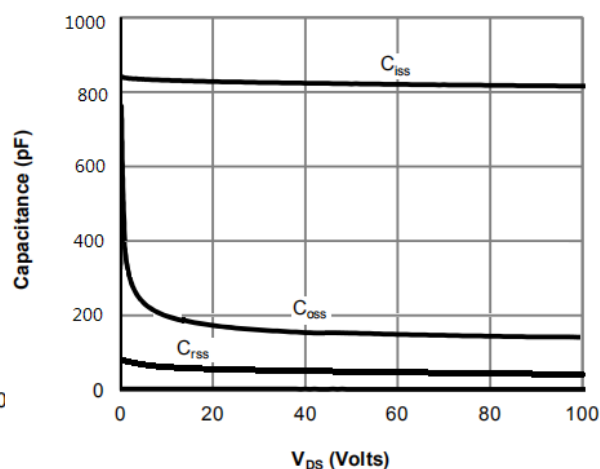
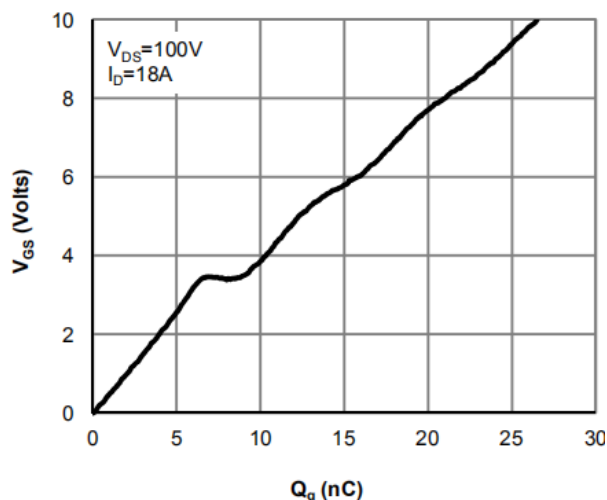
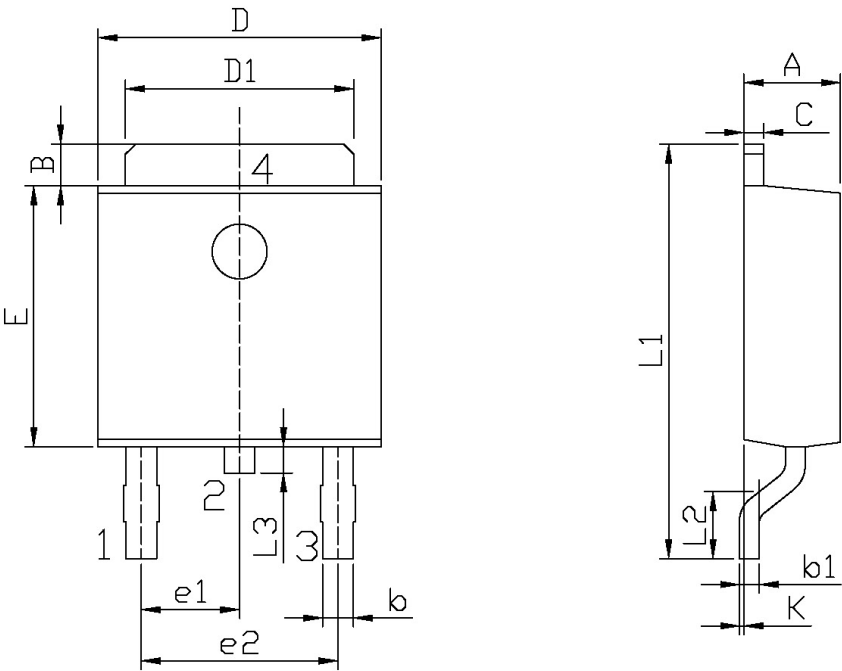


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

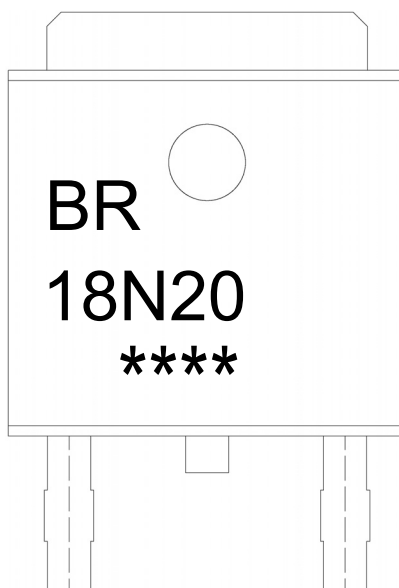


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.70	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

T0-252

印章说明 / Marking Instructions



说明：

BR： 为公司代码

18N20： 为型号代码

****： 为生产批号代码，随生产批号变化。

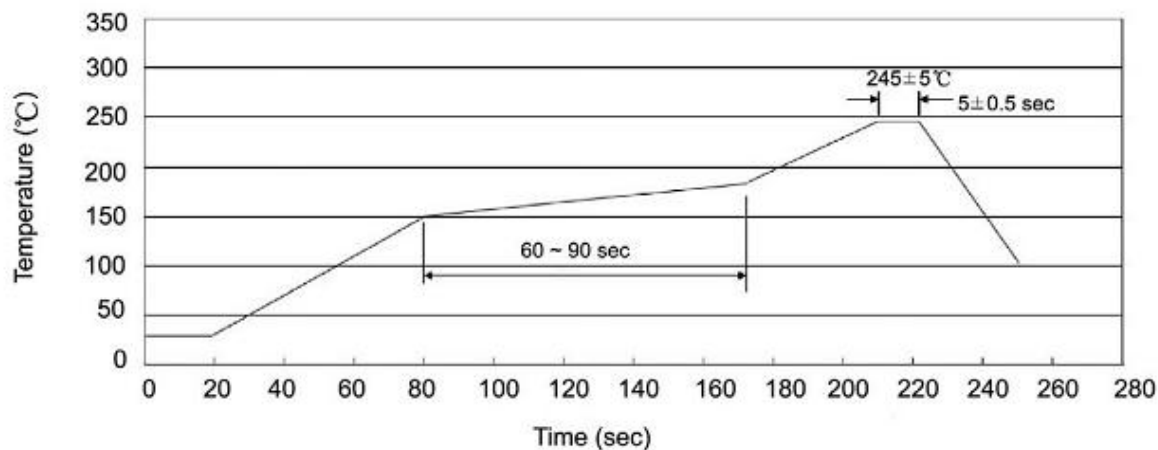
Note:

BR: Company Code

18N20: Product Type.

****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	5	25,000	13" ×16	360×360×50	385×257×392

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

使用说明 / Notices